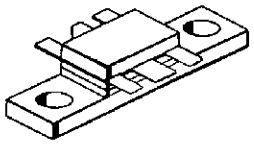
SGS-THOMSON MICROELECTRONICS

SD1414

RF & MICROWAVE TRANSISTORS 800-900 MHz APPLICATIONS

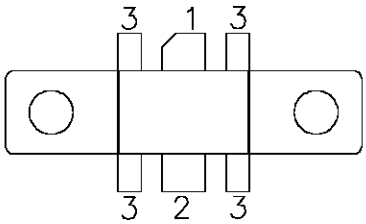
- 836 MHz
- 12.5 VOLTS
- COMMON BASE
- P_{OUT} = 45 W MIN. WITH 4.7 dB GAIN



.230 6LFL (M142)
epoxy sealed

ORDER CODE	BRANDING
SD1414	SD1414

PIN CONNECTION



1. Collector
2. Emitter
3. Base

DESCRIPTION

The SD1414 is a 12.5 V Class C epitaxial silicon NPN planar transistor designed for amplifier applications in the 806 - 866 MHz frequency range. Internal input matching and common base configuration assure optimum gain and efficiency across the entire frequency band. The SD1414 withstands infinite VSWR at rated power output.

ABSOLUTE MAXIMUM RATINGS (T_{case} = 25°C)

Symbol	Parameter	Value	Unit
V_{CBO}	Collector-Base Voltage	36	V
V_{CEO}	Collector-Emitter Voltage	18	V
V_{CES}	Collector-Emitter Voltage	36	V
V_{EBO}	Emitter-Base Voltage	4.0	V
I_C	Device Current	9.0	A
P_{DISS}	Power Dissipation	150	W
T_J	Junction Temperature	+200	°C
T_{STG}	Storage Temperature	– 65 to +150	°C

THERMAL DATA

$R_{TH(j-c)}$	Junction-Case Thermal Resistance	1.2	°C/W

ELECTRICAL SPECIFICATIONS (T_{case} = 25°C)

STATIC

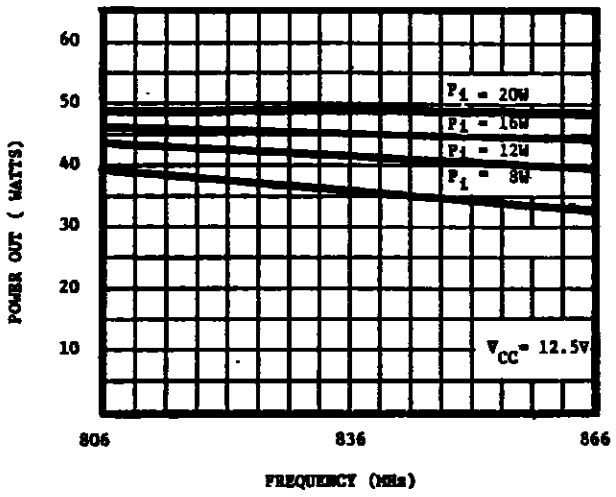
Symbol	Test Conditions		Value			Unit
			Min.	Typ.	Max.	
BV_{CES}	I_C = 50mA	V_{BE} = 0V	36	—	—	V
BV_{CEO}	I_C = 50mA	I_B = 0mA	18	—	—	V
BV_{EBO}	I_E = 10mA	I_C = 0mA	4.0	—	—	V
I_{CBO}	V_{CB} = 15V	I_E = 0mA	—	—	5	mA
h_{FE}	V_{CE} = 5V	I_C = 1A	5	—	200	—

DYNAMIC

Symbol	Test Conditions			Value			Unit
				Min.	Typ.	Max.	
P_{OUT}	f = 836 MHz	P_{IN} = 15 W	V_{CE} = 12.5 V	45	—	—	W
G_P	f = 836 MHz	P_{IN} = 15 W	V_{CE} = 12.5 V	4.7	—	—	dB
C_{OB}	f = 1 MHz	V_{CB} = 12.5 V		—	80	—	pF

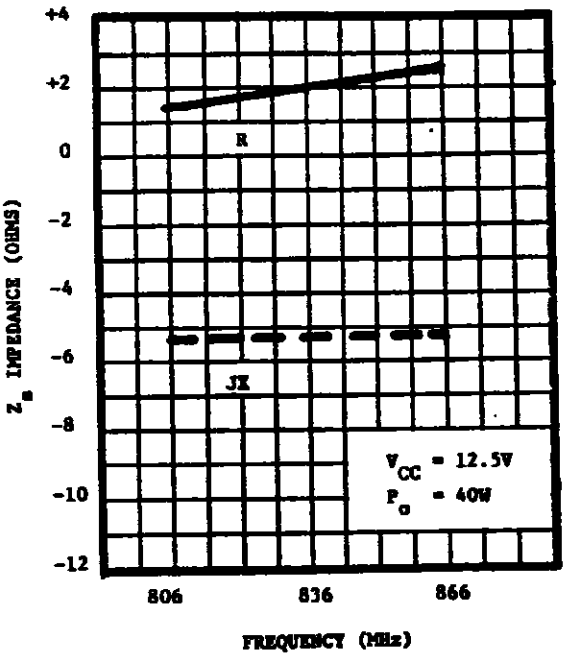
TYPICAL PERFORMANCE

POWER OUTPUT vs FREQUENCY

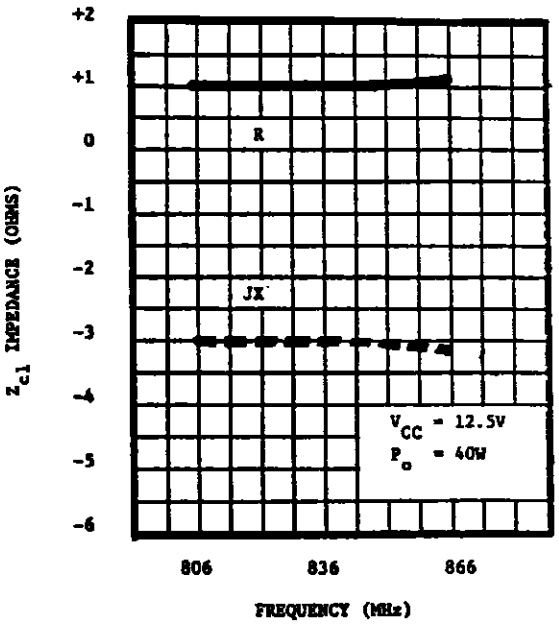


IMPEDANCE DATA

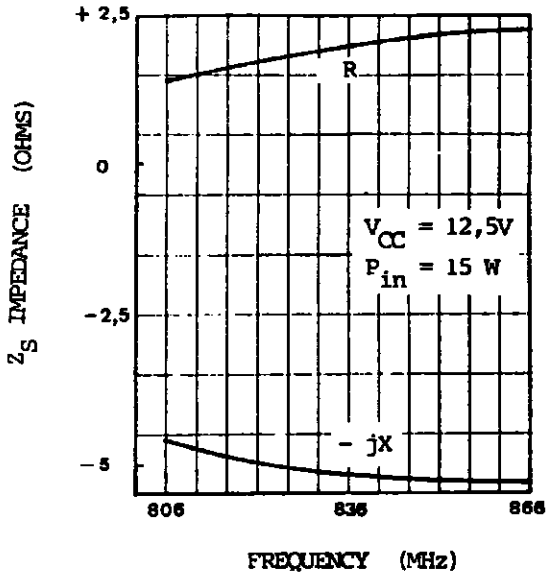
TYPICAL INPUT IMPEDANCE



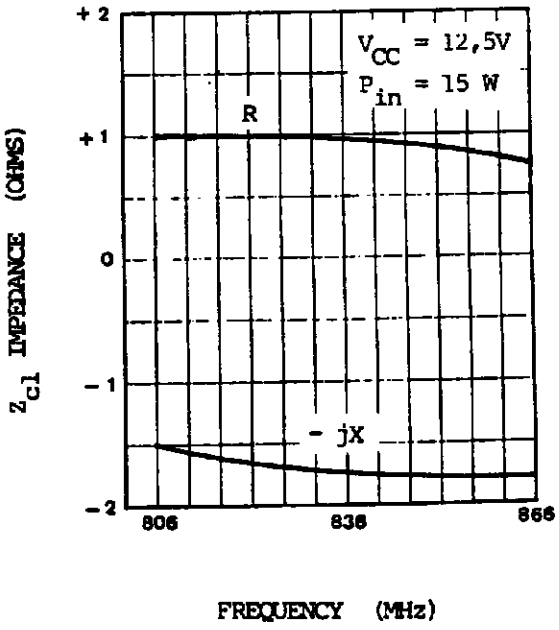
TYPICAL COLLECTOR LOAD IMPEDANCE



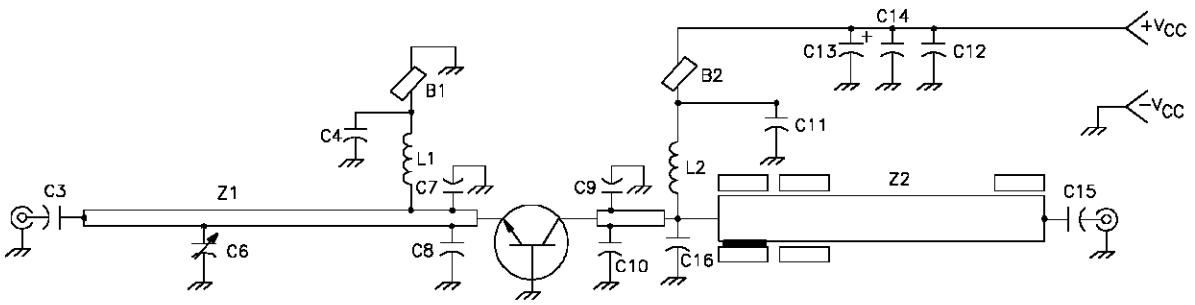
TYPICAL INPUT IMPEDANCE



TYPICAL COLLECTOR LOAD IMPEDANCE



TEST CIRCUIT



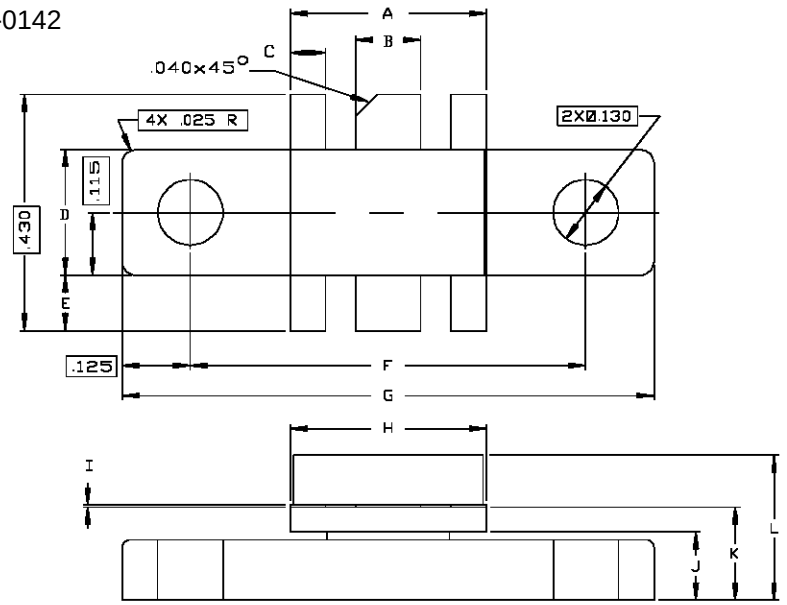
C1, C4 : 5pF ATC 100 mils Chip Capacitor
C2 : 1 - 12pF Variable Capacitor
C3 : .6 - 6pF Variable Capacitor
C5 : 2pF "A" Size Chip Capacitor
C6, C7 : .6 - 12pF Voltronic Variable Capacitor

C8 : 480pF ATC 100 mils Chip Capacitor
C9 : 47µF, 63V, Electrolytic Capacitor
C10 : 1000pF Unelco Capacitor
L1, L2 : 5 Turns #24 AWG Enamel

Board Material: 3M-K-6098-11 12.9 mils Thick

PACKAGE MECHANICAL DATA

Ref.: Dwg. No.12-0142



SGS-THOMSON MICROELECTRONICS		
	MINIMUM Inches/mm	MAXIMUM Inches/mm
A	.355/9,02	.365/9,27
B	.115/2,92	.125/3,18
C	.075/1,91	.085/2,16
D	.225/5,72	.235/5,97
E	.090/2,29	.110/2,79
F	.720/18,29	.730/18,54
G	.970/24,64	.980/24,89
H	.355/9,02	.365/9,27
I	.004/0,10	.006/0,15
J	.120/3,05	.130/3,30

CONT'D		
	MINIMUM Inches/mm	MAXIMUM Inches/mm
K	.160/4,06	.180/4,57
L	.230/5,84	.260/6,60